

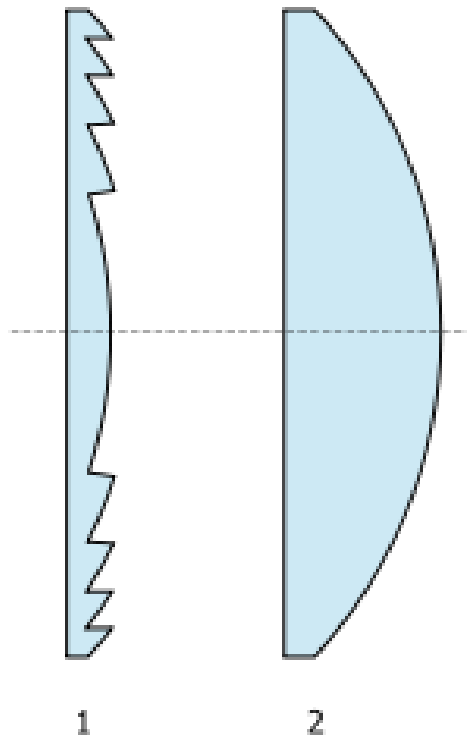
# The PCM is dead! Long Live O-PCM!

Cosmin-Constantin Popescu<sup>1</sup>, Khoi Phuong Dao<sup>1</sup>, Luigi Ranno<sup>1</sup>, Brian Mills<sup>1,7</sup>, Louis Martin<sup>1</sup>, Yifei Zhang<sup>1</sup>, Carlos Rios<sup>1,4</sup>, Qingyang Du<sup>1,2</sup>, Kiumars Aryana<sup>5</sup>, Steven Vitale<sup>3</sup>, Vladimir Liberman<sup>3</sup>, Paul Miller<sup>1,3</sup>, Christopher Roberts<sup>3</sup>, David Bono<sup>1</sup>, Brian Neltner<sup>1</sup>, Myungkoo Kang<sup>6</sup>, Kathleen Richardson<sup>6</sup>, Hyung Bin Bae<sup>8</sup>, Hyun Jung Kim<sup>5</sup>, Juejun Hu<sup>1</sup>

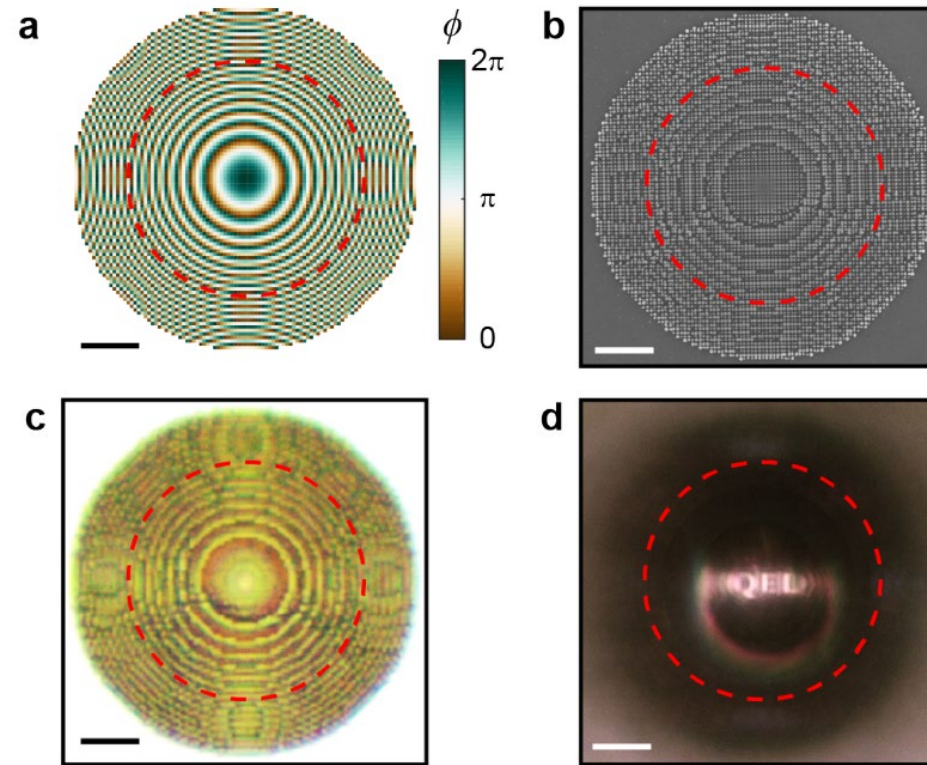
1. Department of Materials Science and Engineering, Massachusetts Institute of Technology
2. Research Center for Intelligent Optoelectronic Computing, Zhejiang Lab
3. Lincoln Laboratory, Massachusetts Institute of Technology, Lexington, MA, United States
4. Department of Materials Science and Engineering, University of Maryland, College Park, MD, United States
5. NASA Langley Research Center, Hampton, VA, United States
6. CREOL, The College of Optics and Photonics, University of Central Florida, Orlando, FL, United States
7. Charles Stark Draper Laboratory, Cambridge, MA, United States
8. KAIST Analysis Center, Korea Advanced Institute of Science and Technology, Daejeon, Korea



# Diffractive optics to sub-wavelength scale E-field phase control



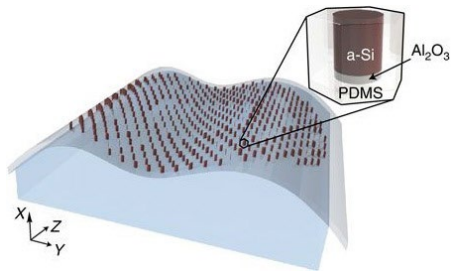
[https://en.wikipedia.org/wiki/Fresnel\\_lens](https://en.wikipedia.org/wiki/Fresnel_lens)



*Nature* 10, 1 (2019)

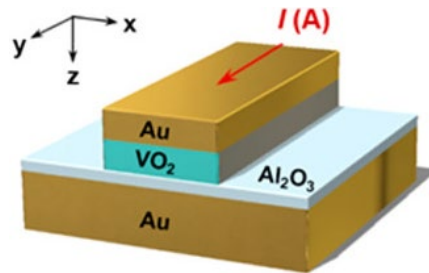
# Active Metasurfaces to PCM Metasurfaces

## Mechanical



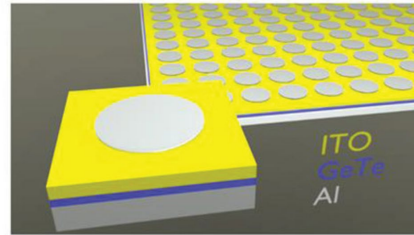
*Nat. Commun.* **7**, 11618 (2016)

## Phase transition



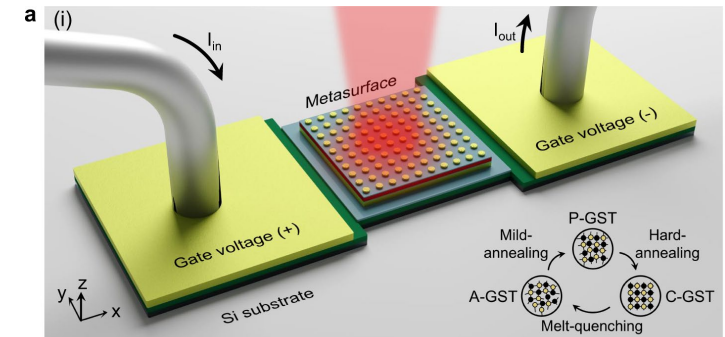
*Nano Lett.* **19**, 3961 (2019)

## GeTe



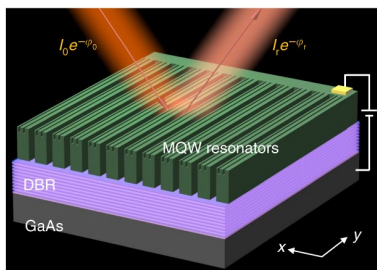
*Adv. Opt. Mater.* **7.18** (2019)

## Ge<sub>2</sub>Sb<sub>2</sub>Te<sub>5</sub>



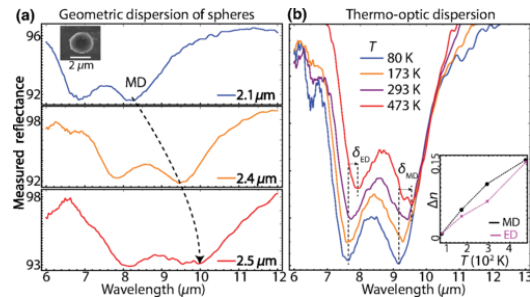
*Nat. Comm.* **13**, 1696 (2022)

## Electro-optic



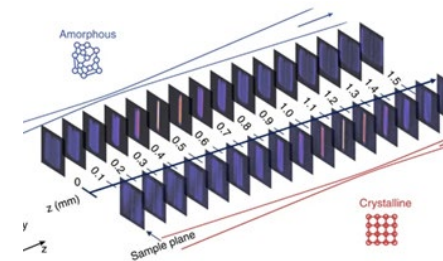
*Nat. Commun.* **10**, 3654 (2019)

## Thermo-optic



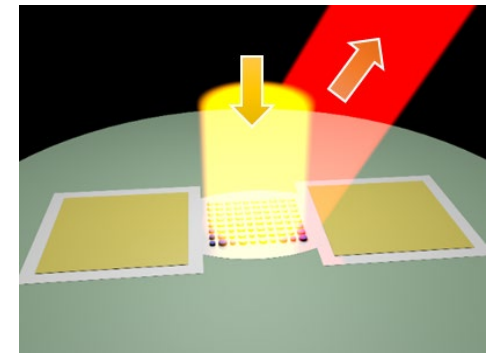
*Phys. Rev. Appl.* **10**, 044029 (2018)

## Ge<sub>3</sub>Sb<sub>2</sub>Te<sub>6</sub>



*Light Sci. Appl.* **6**, e17016 (2017)

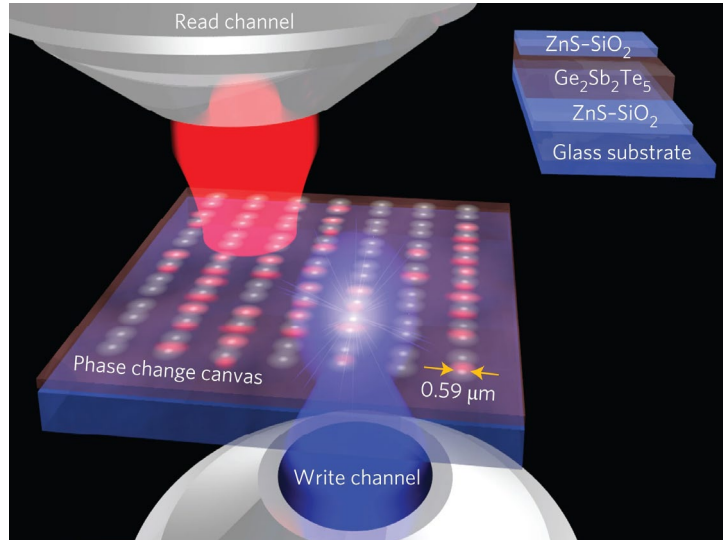
## Ge<sub>2</sub>Sb<sub>2</sub>Se<sub>4</sub>Te



*Nat. Nanotech.* **16**, 661-666 (2021)

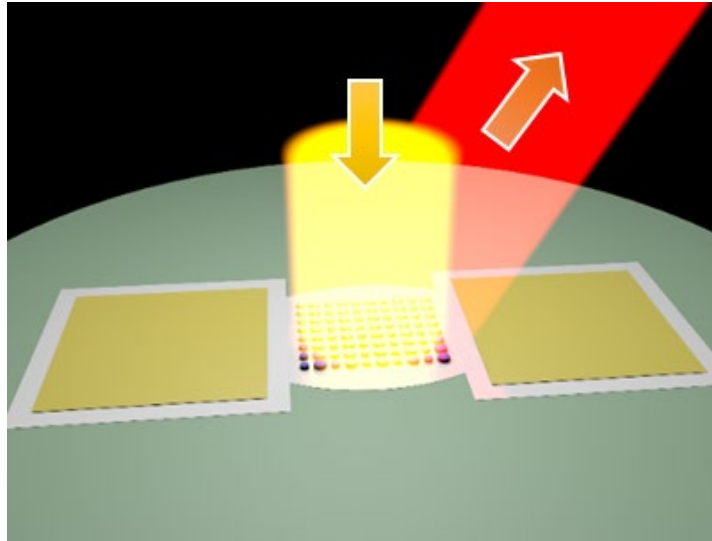
# Switching PCM

## Laser writing

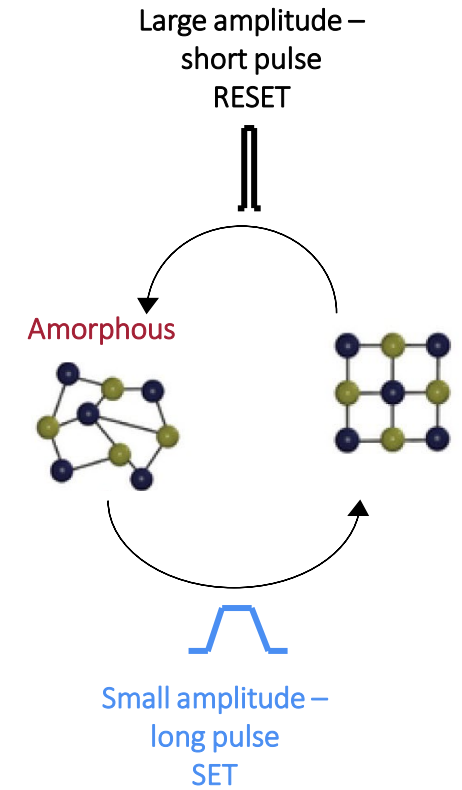


*Nat. Photonics* **10**, 60 (2016)

## Electro-thermal heating

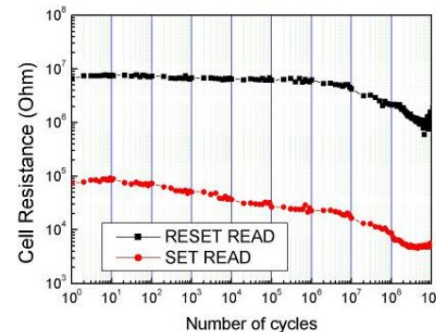
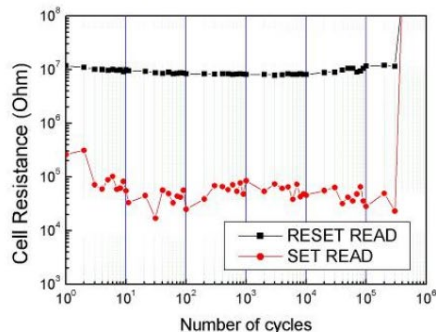
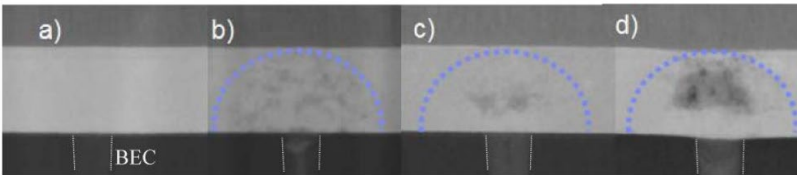
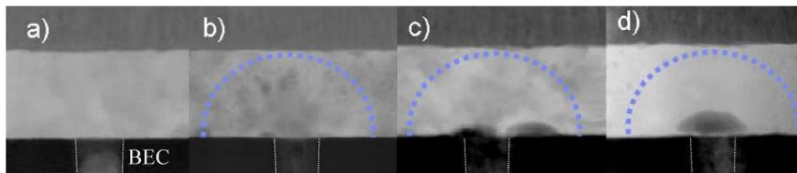


*Nat. Nanotech.* **16**, 661-666 (2021)



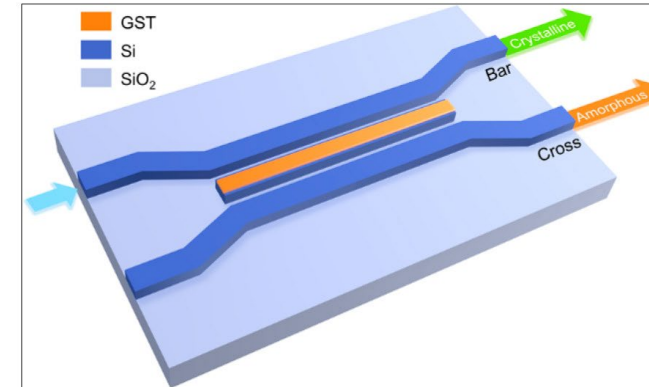
# Endurance of PCMs

- Electrical phase change memory – resistance
- Optical phase change device – transmission/reflection
  - PCM optical properties



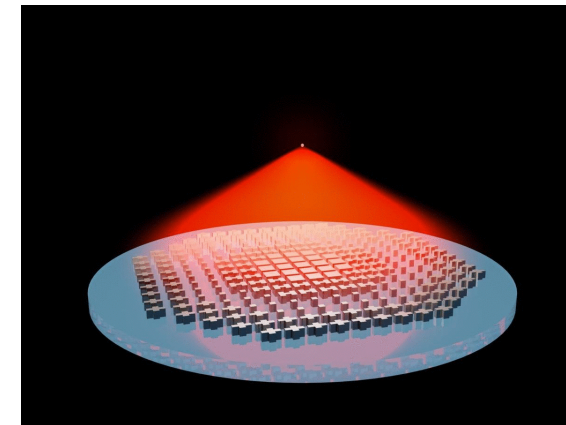
Chen et al. *IEEE Int. Memory Workshop.* (2009)

## Photonic Integrated Circuits Length in the in-plane direction



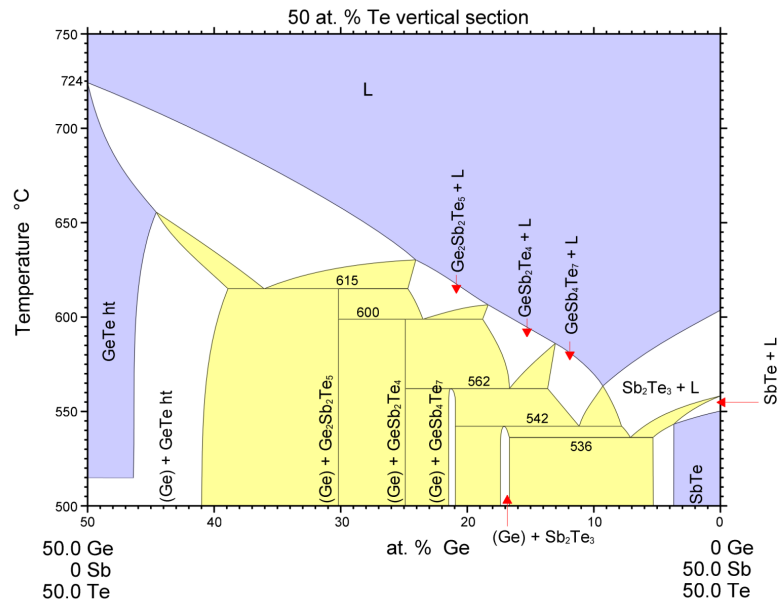
*ACS Photonics*, **6**, 2, 553–557, (2019)

## Free-space optics Phase accumulation along thickness



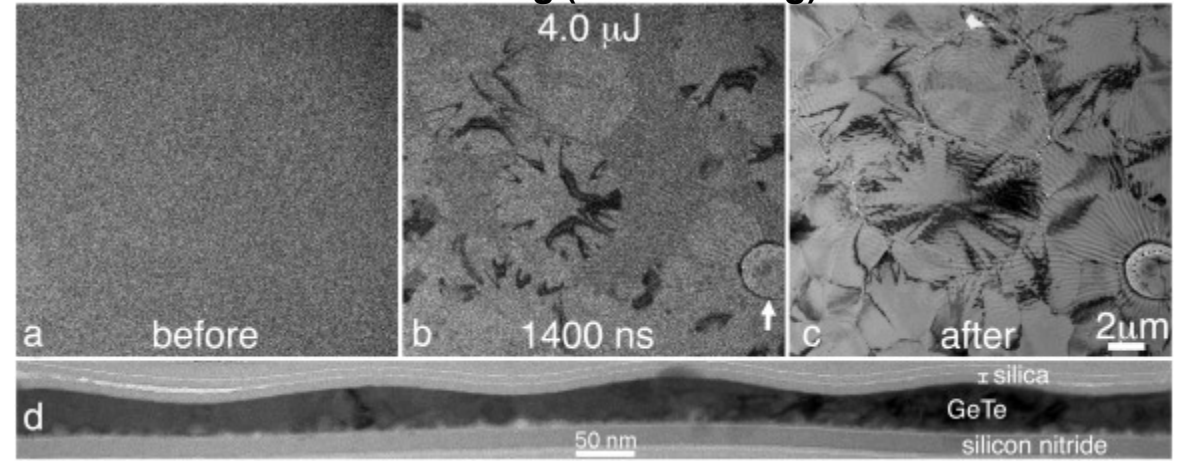
*Nat. Commun.* **12**, 1225 (2021)

### Incongruent melting



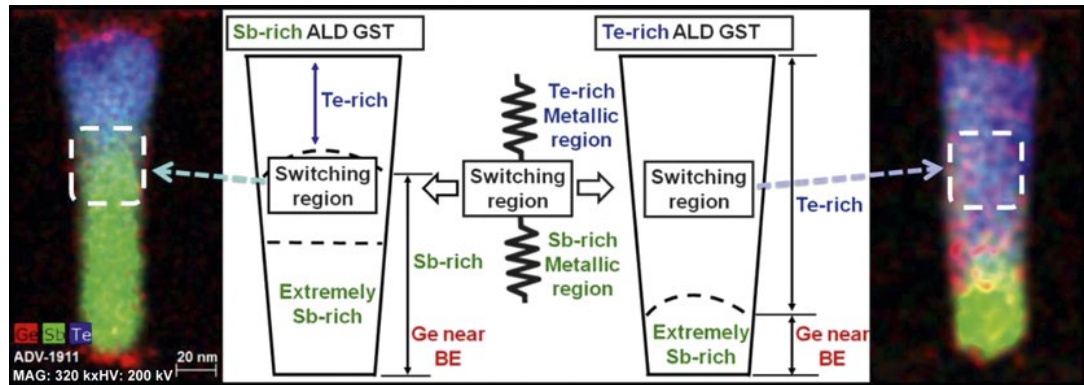
ASM Phase Diagram Database™ ©ASM International 2006. Diagram No. 990450

### Dewetting (laser heating)



Thin Solid Films 571. 39-44 (2014)

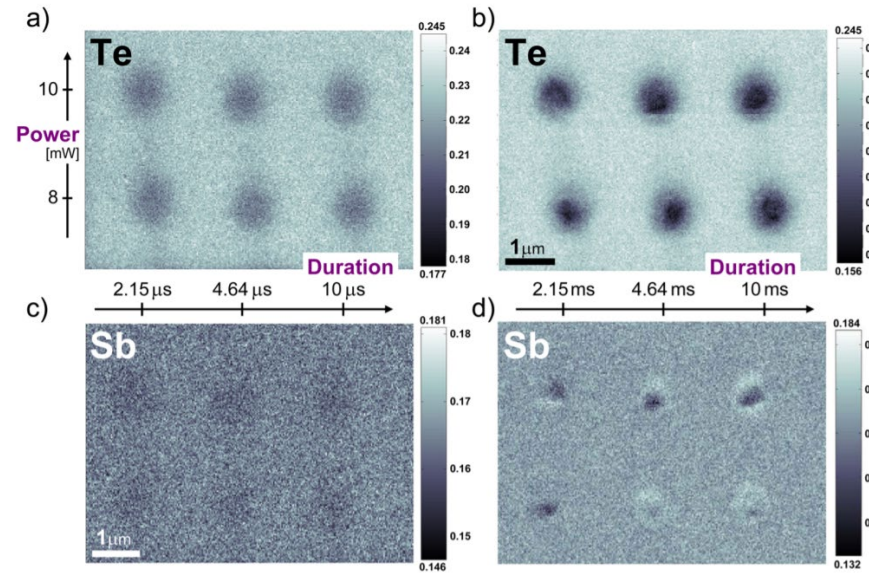
### Pore formation and elemental segregation



MRS Bull. 44, 710-714 (2019)

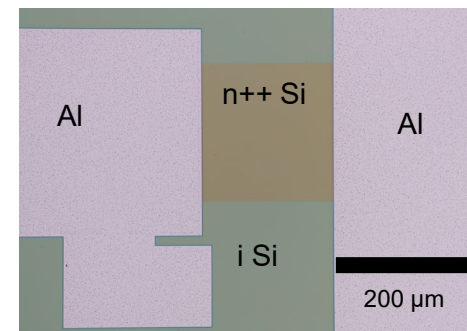
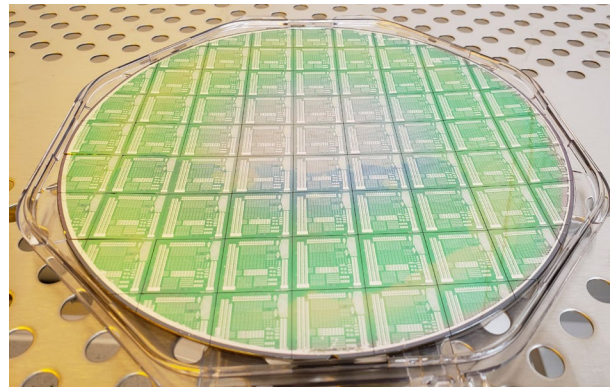
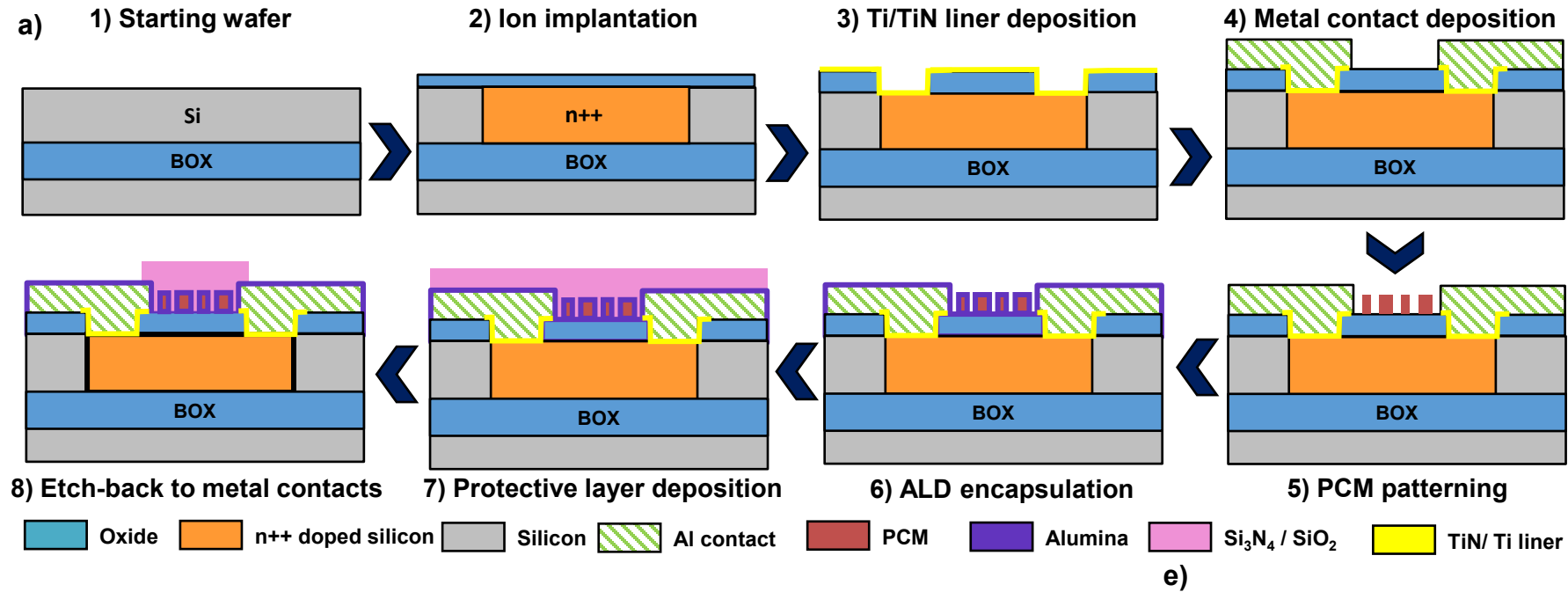
### Thermal migration

### Volatilization



J. Electrochem. Soc. 158 10 (2011)

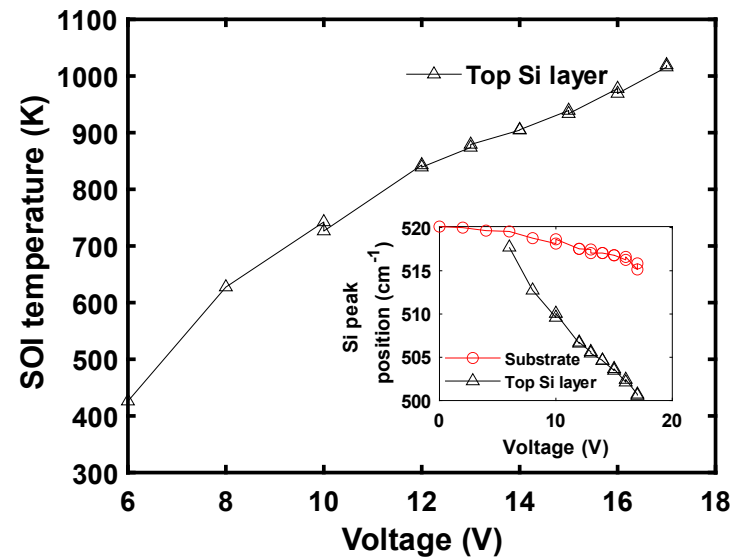
# Platform fabrication



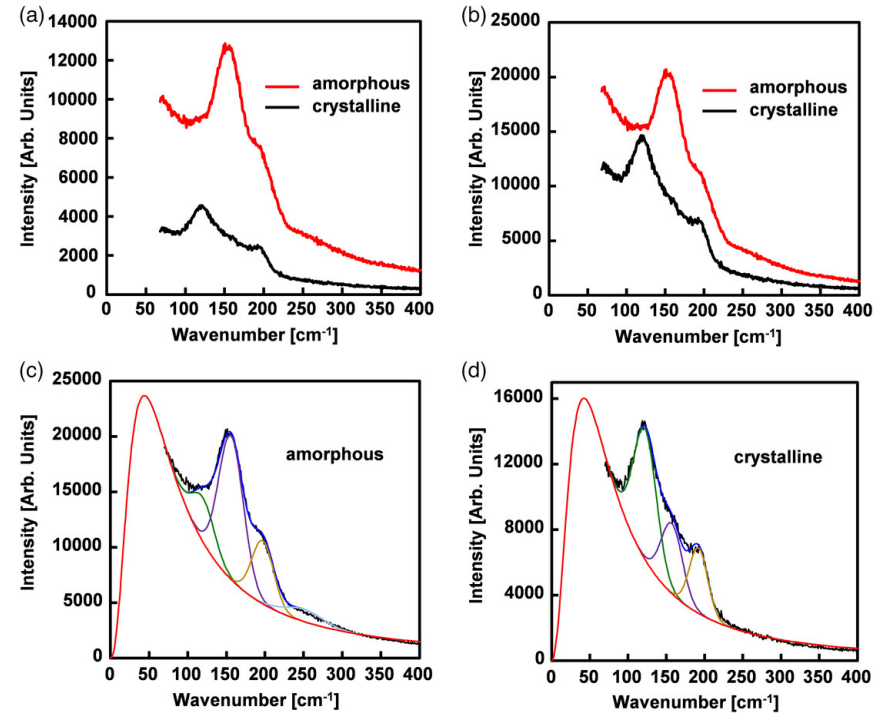
# On chip TTT diagrams

Adv. Photonics Research 3. 10 (2022)

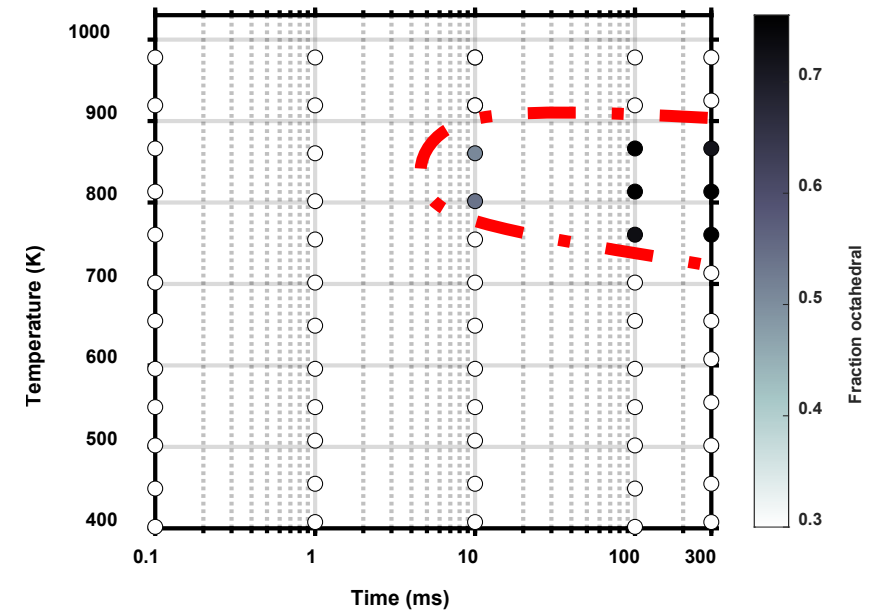
Temperature verification steady state against COMSOL simulations



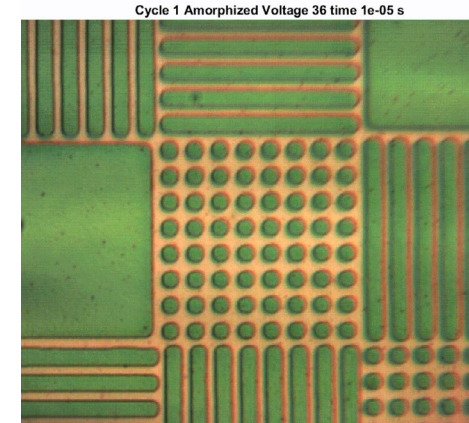
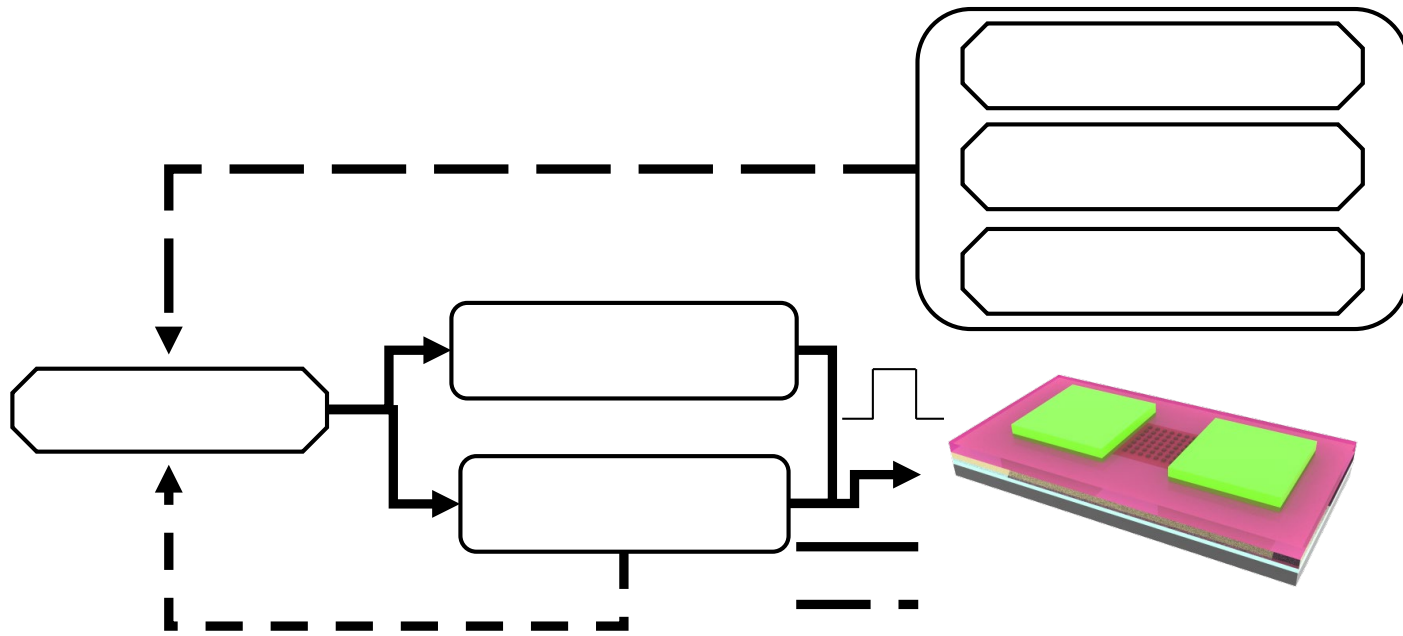
GSST Raman peak fitting  
Ge-6Se and Ge-4Se



Voltage & Pulse width  $\Rightarrow$   
Temperature & Ge-6Se peak



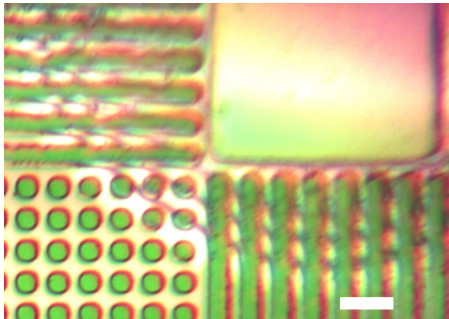
# Unraveling failure mechanisms in **optical** PCMs



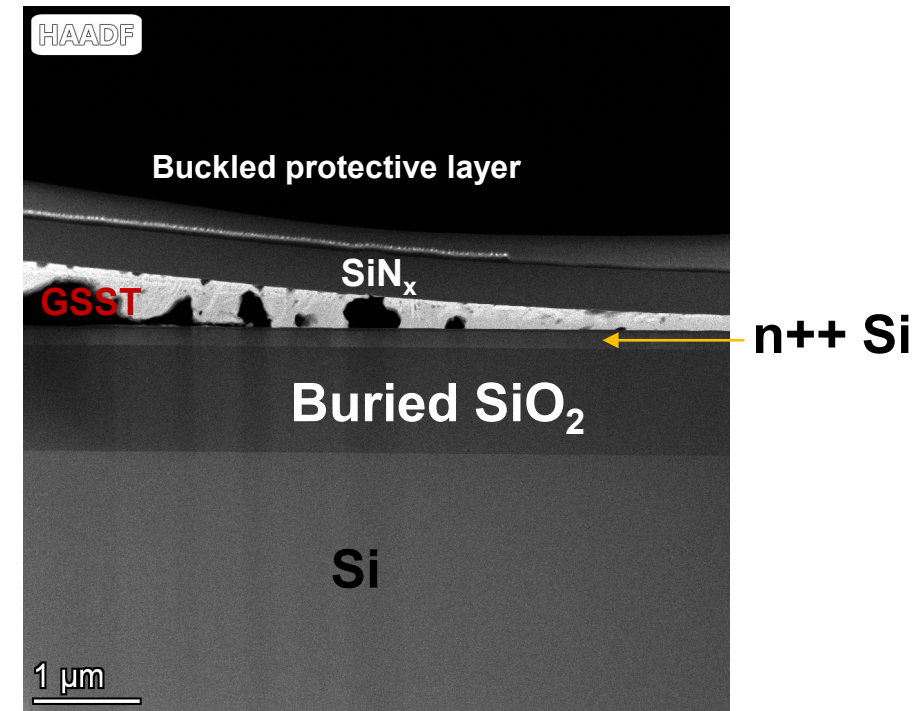
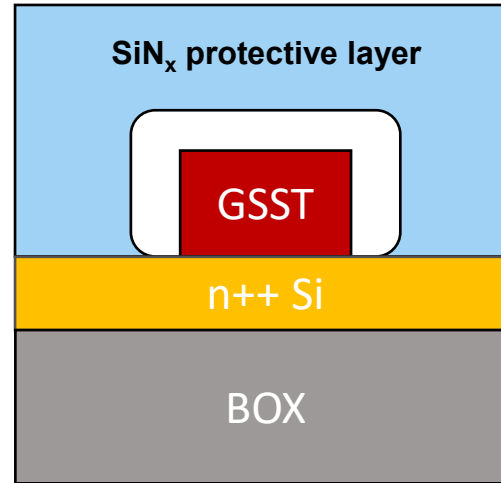
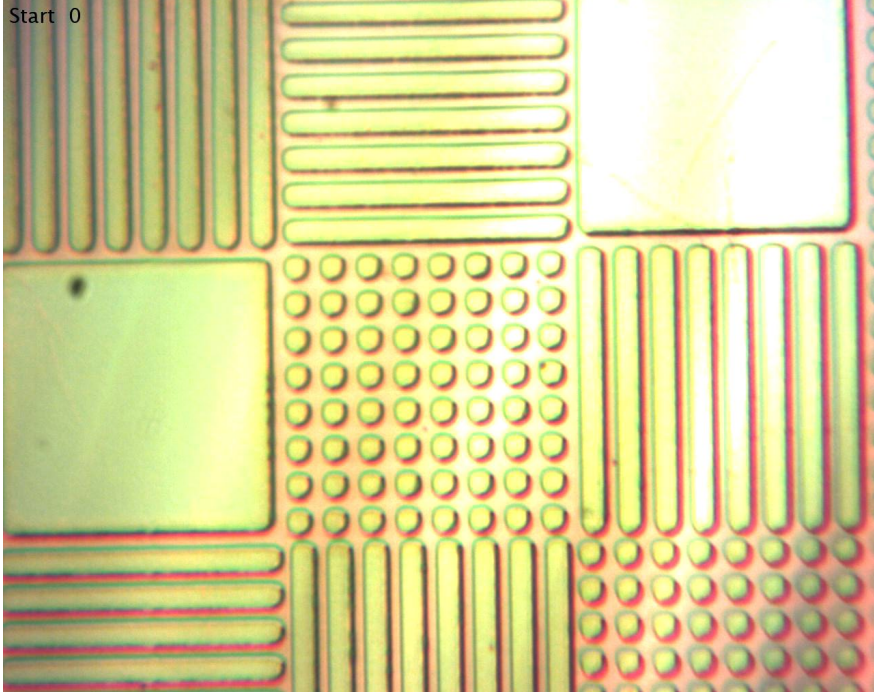
*In situ* concurrent structural and optical characterizations

# Delamination & Adhesion

Capping layer  
delamination

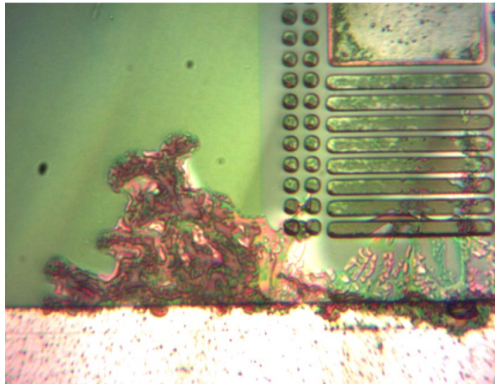


Fringes highlight  
varying void thickness

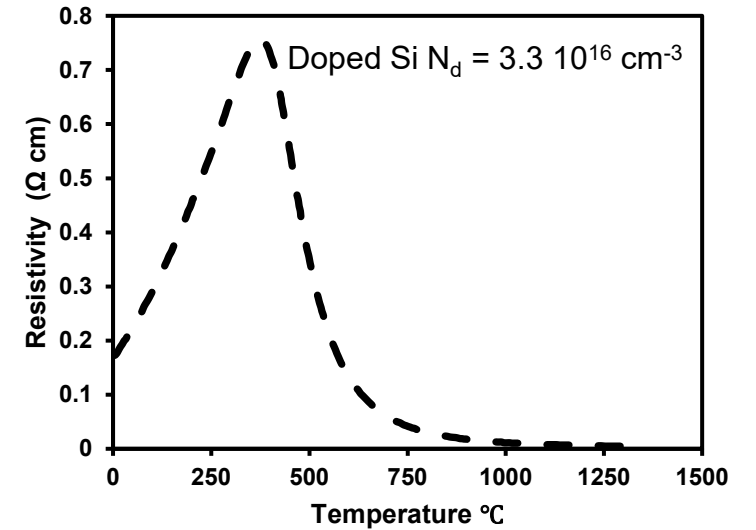
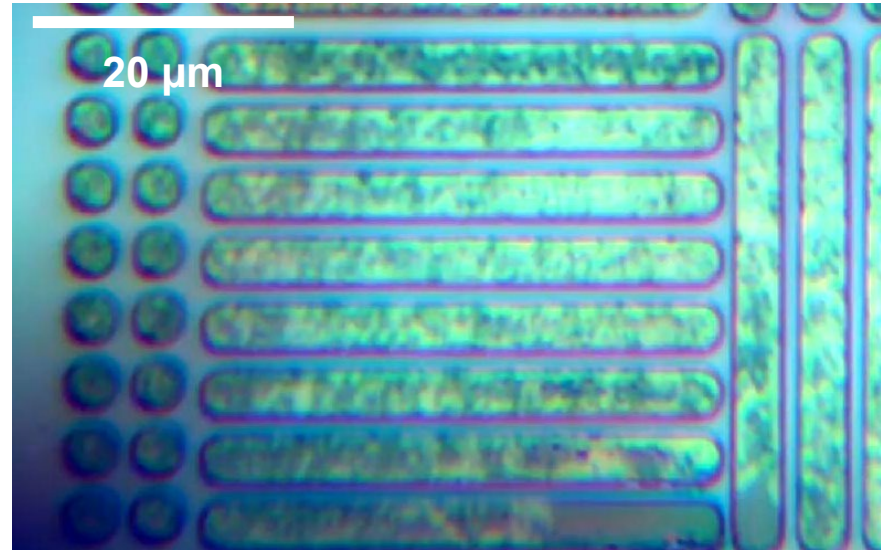


**Potential solution:**  
Restrict dimensions of thin films  
(e.g. metasurfaces);  
Adjust material choice for improved  
adhesion substrate-PCM and PCM-  
protective layer

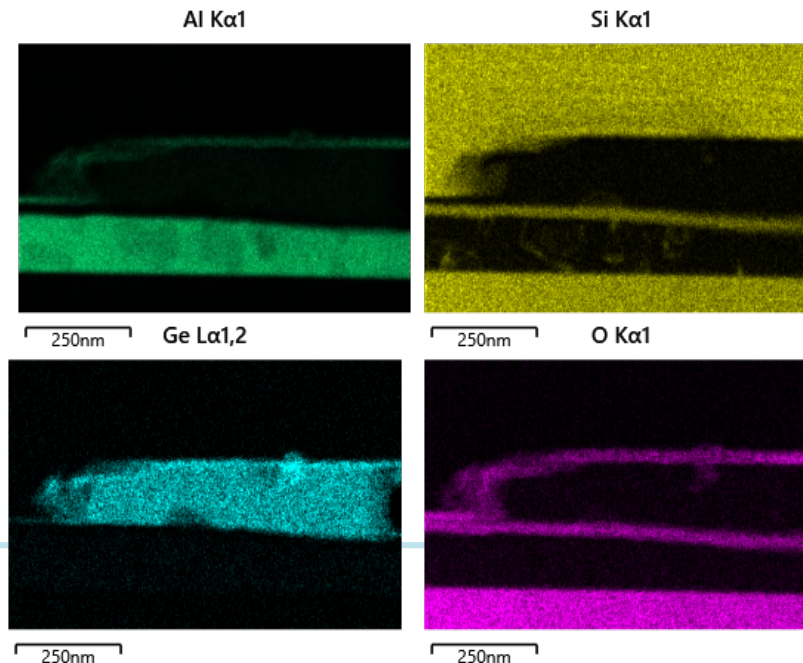
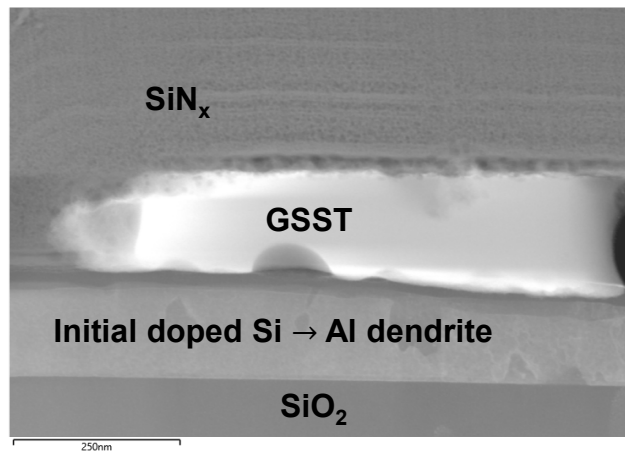
# Metal electromigration /Current crowding



Metal contact electromigration

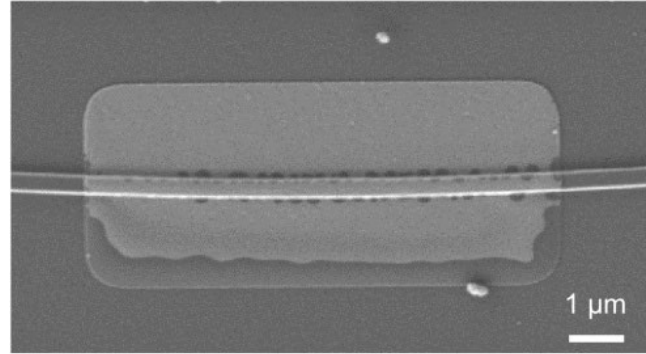
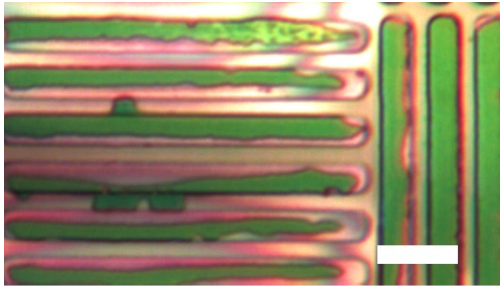


Cabal, A. R. *ETSIT UMP*, Ph.D. Thesis (2015)



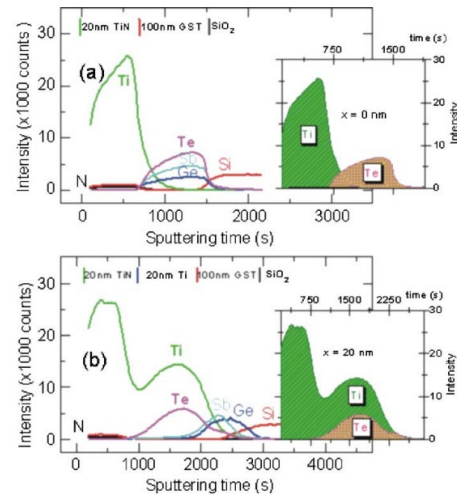
**Potential solutions:**  
 Reshape heater – wider contact region  
 Improved heat sink; Time delay for cooling  
 Downside: large delay for switching applications  
 Small device area

# Dewetting / fluid instability

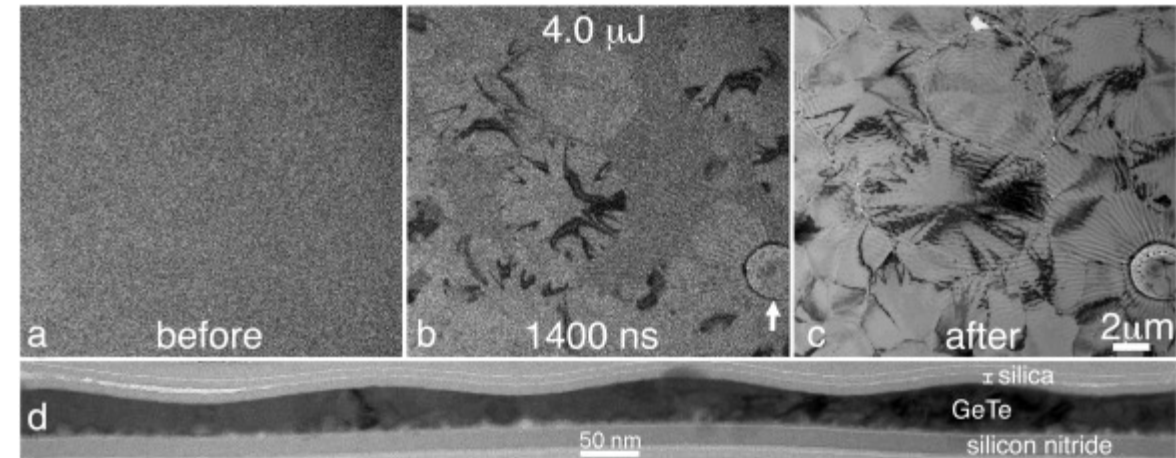


Dewetting of  $\text{Sb}_2\text{Se}_3$  thin film on Si waveguide

Dewetting  
& fluid  
instability



*Appl. Phys. Lett.* **90**, 051908 (2007)

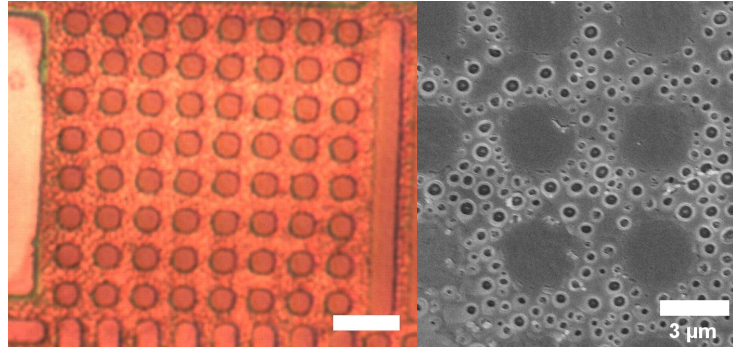


*Thin Solid Films* **571**, 39-44 (2014)

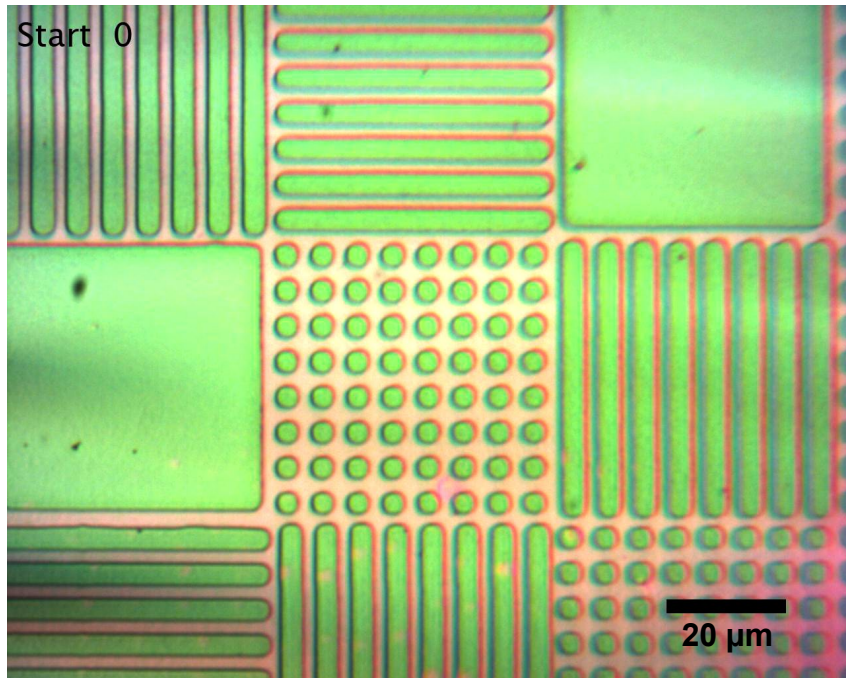
**Potential solutions:**  
**Restrict aspect ratio**  
**Material choice for improved adhesion to substrate**

**Downside: Potential losses due to adhesion materials (e.g. Ti or TiN) and parasitic reactions ( $\text{TiTe}_2$  formation)**

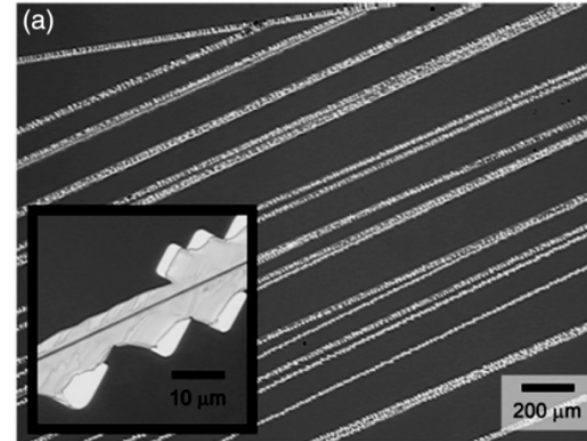
# Damage & pore formation due to H-release



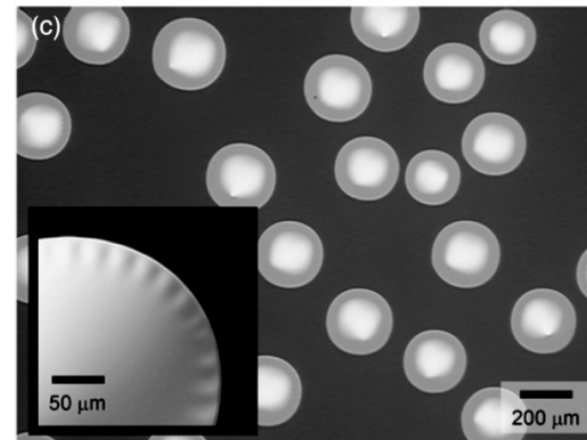
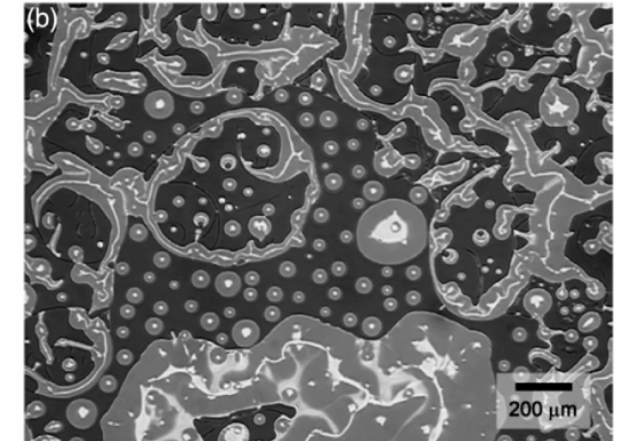
H-release from capping layer



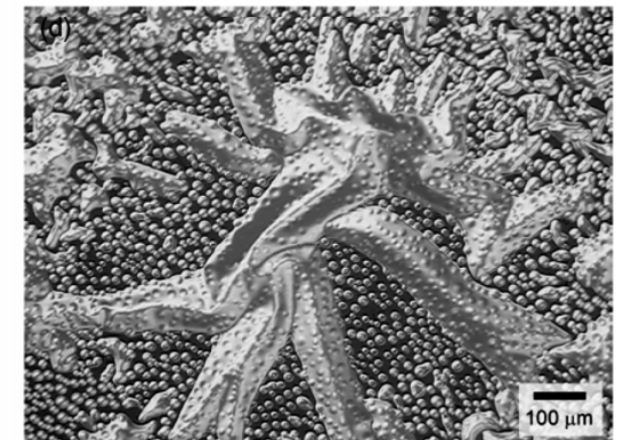
SiN<sub>x</sub> on InP



SiN<sub>x</sub> on InP



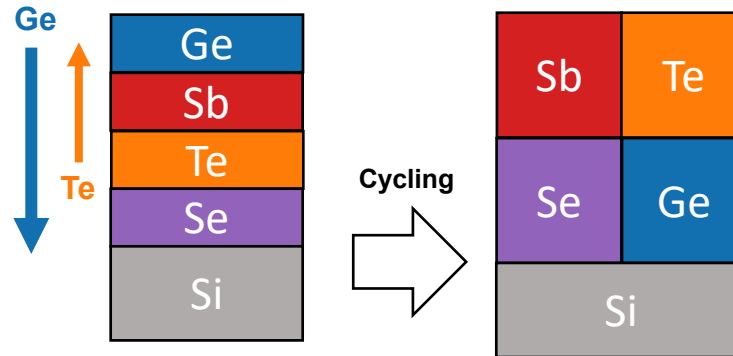
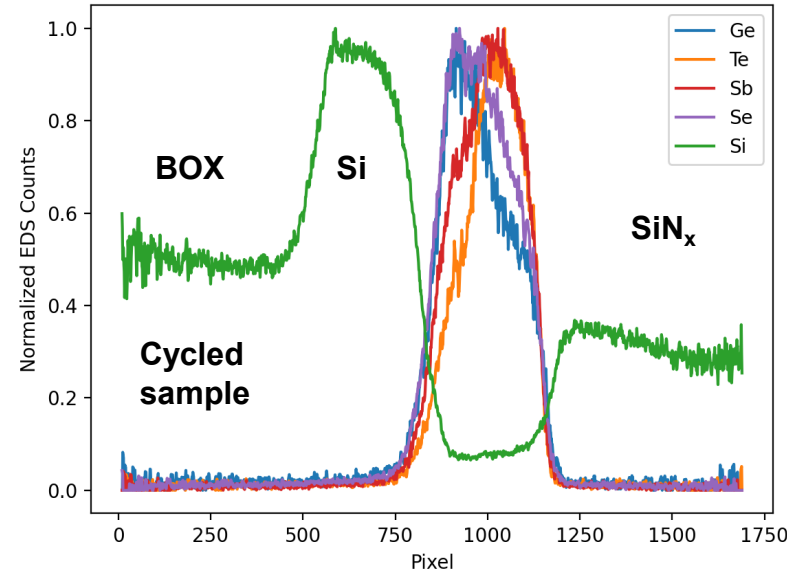
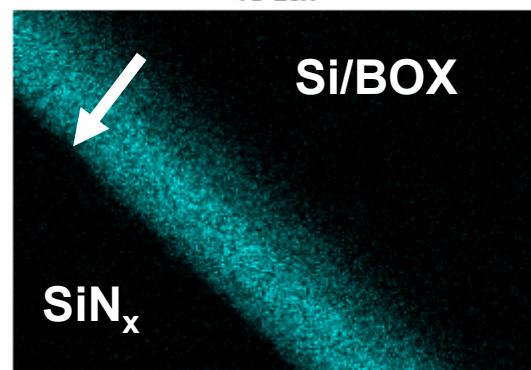
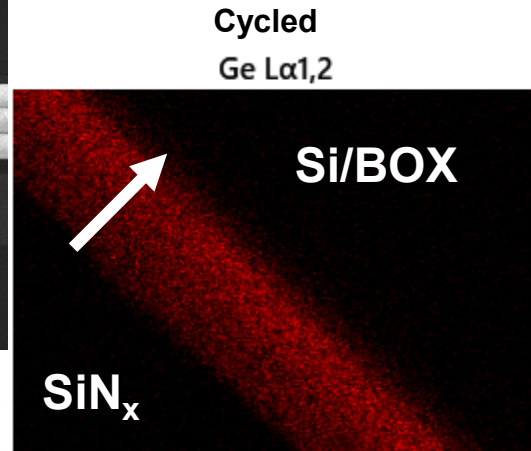
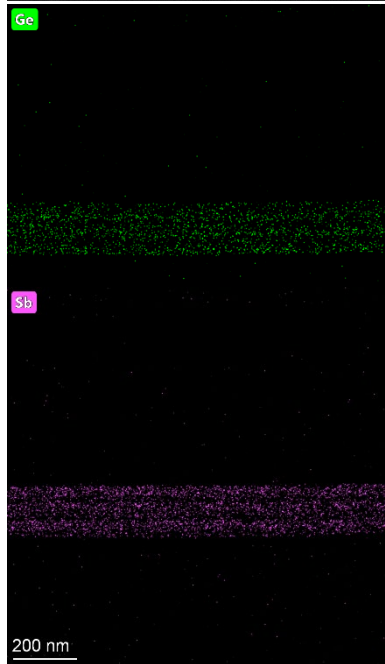
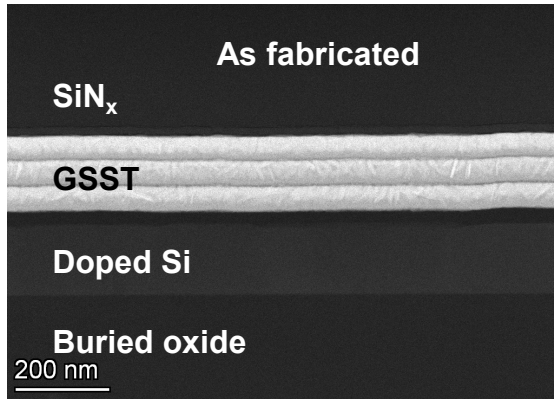
SiN<sub>x</sub> on Si



SiN<sub>x</sub> on InP

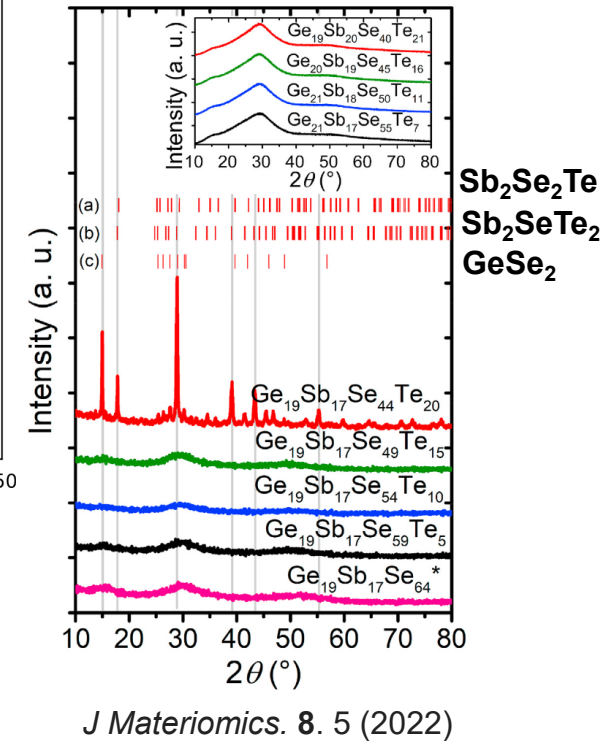
Hughey & Cook, *Thin Solid Films* **460**. 1-2 (2004)

# Elemental migration



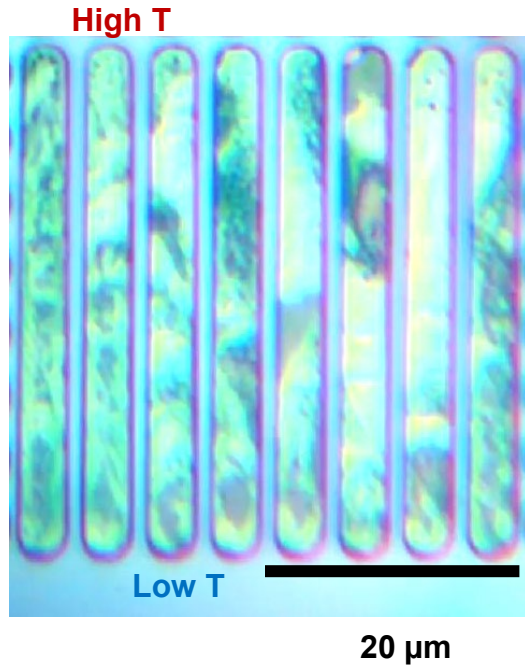
Based on the vapor pressure of the elements.

## 13 Melt-quench bulk sputter targets

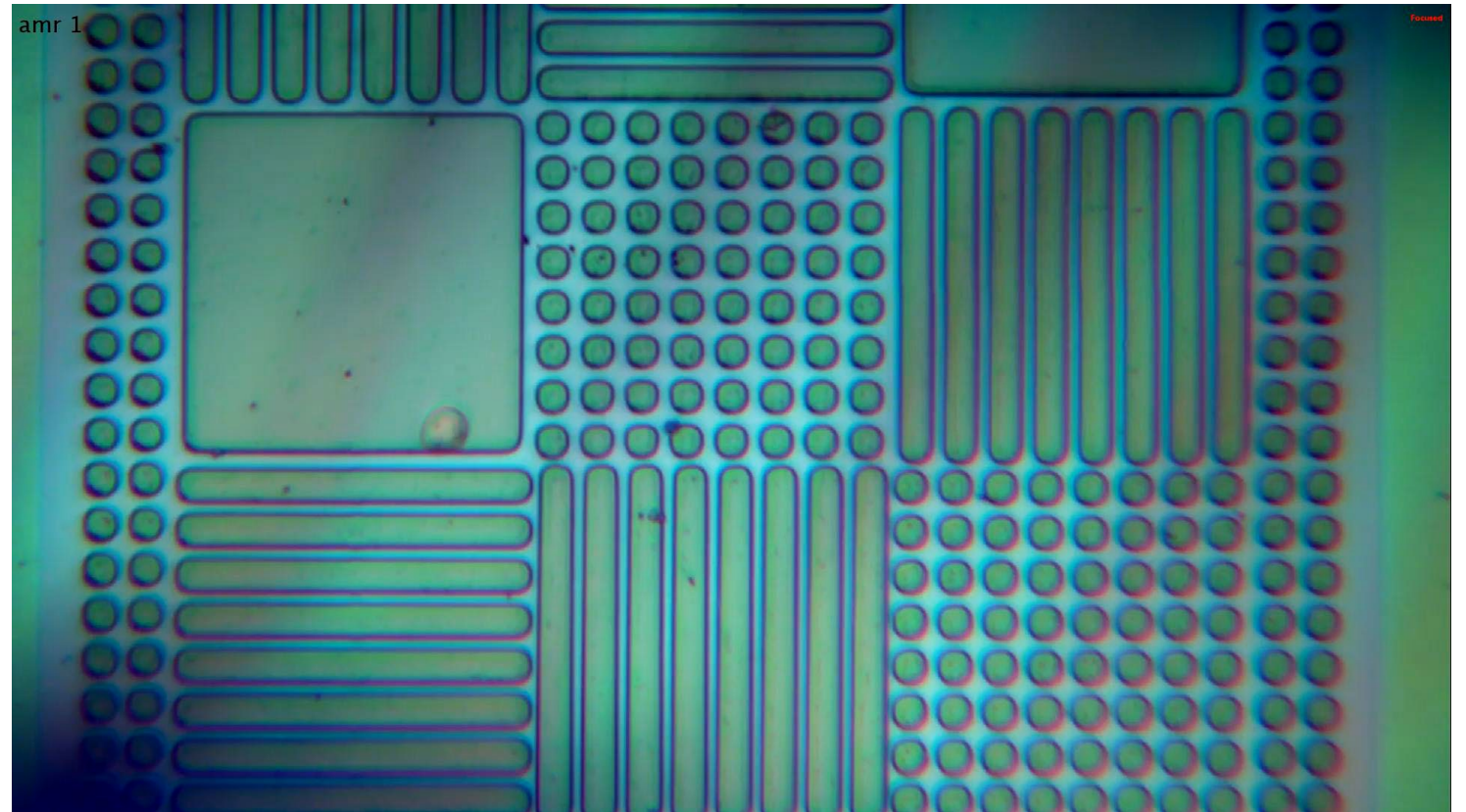


**Potential solution:**  
 Repeated amorphization may remove elemental segregation  
 Downside: Thermal stresses

# Mitigating elemental migration

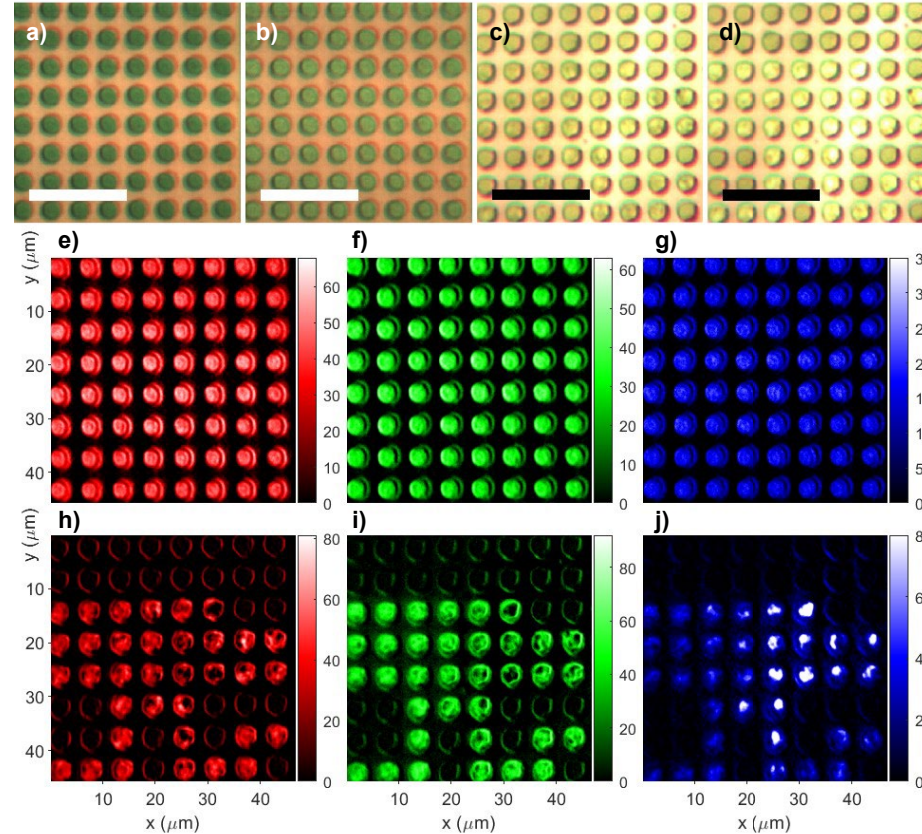


Over-amorphization

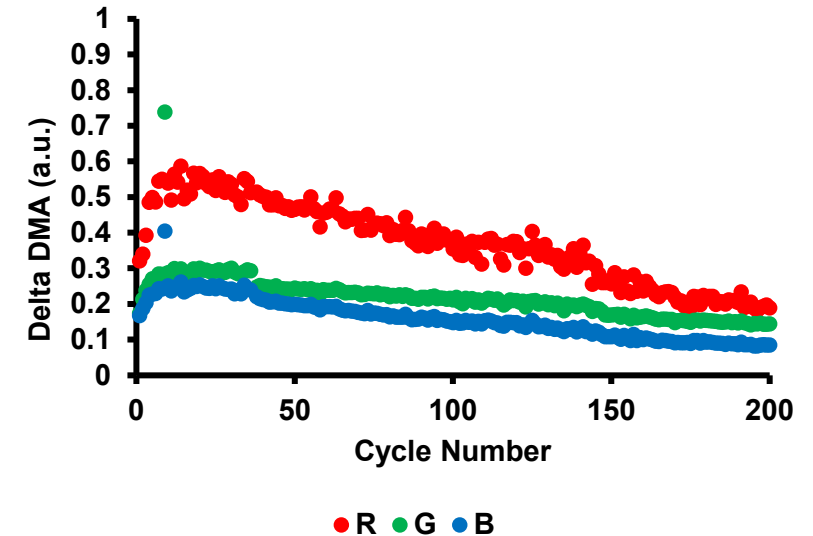


# Semi-quantitative analysis for free-space devices

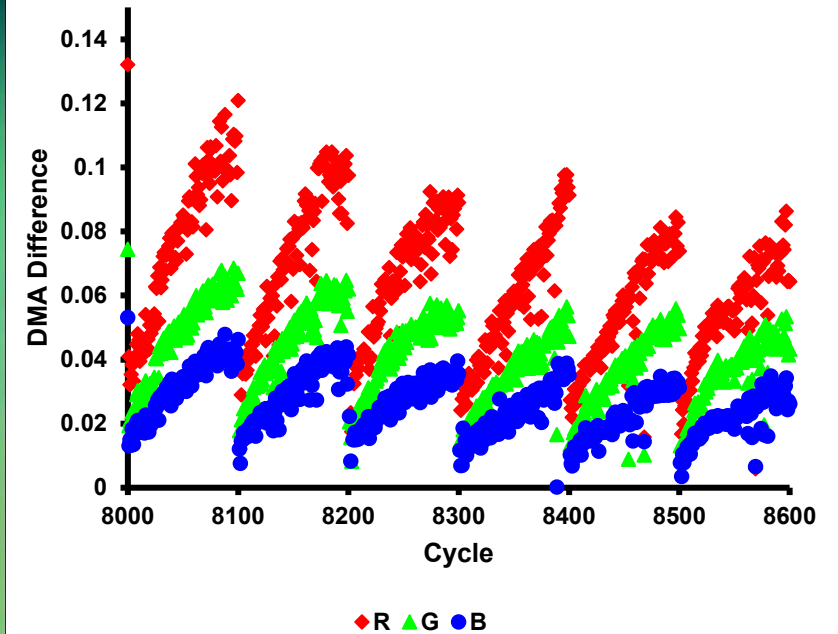
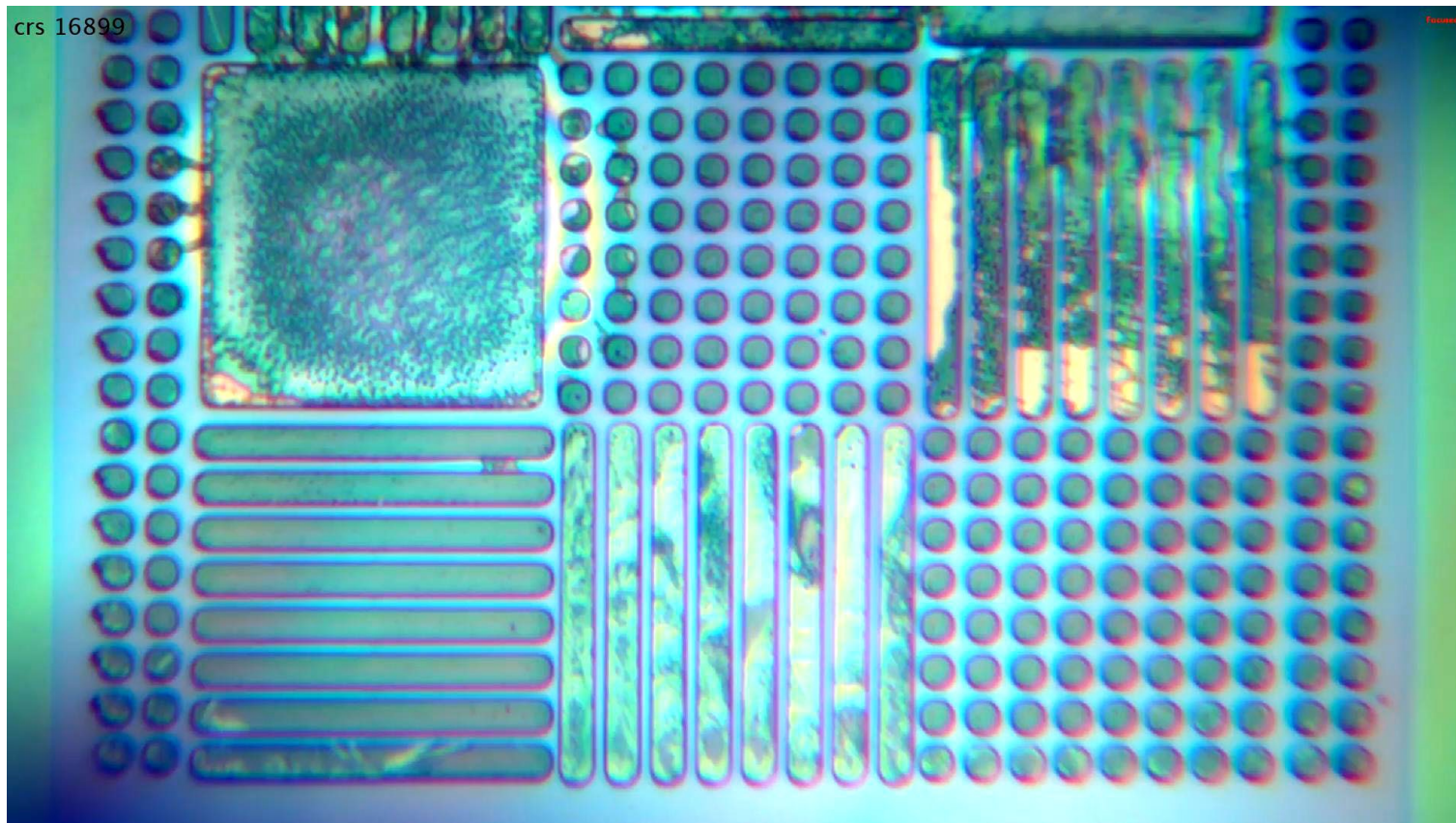
- **Image collection**
  - Amorphous (State 1)
  - Crystalline (State 2)
- **Difference between pixel values**
- **Filter pixels with value above threshold – binary mask**
  - Heuristic approach for threshold selection
- **Average values in filtered (PCM/Switching) region**
- **Normalize by average outside filtered region (Background)**
  - Brightness instability
- **Difference of ratios**
  - Proxy for contrast over time



$$\Delta = \left[ \frac{RGB_{PCM}}{RGB_{Bckg}} \right]_{Cr} - \left[ \frac{RGB_{PCM}}{RGB_{Bckg}} \right]_{Am}$$



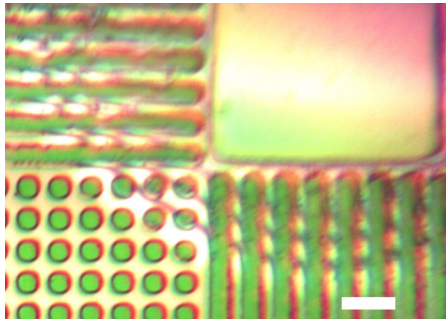
# Repeated longer amorphization pulse (every 100 cycles)



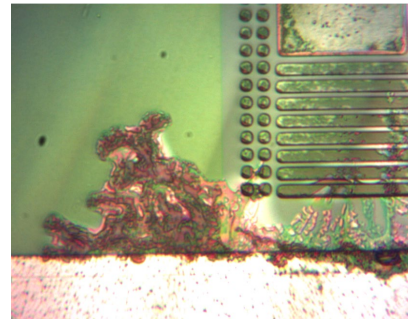
Typical operation below full amorphization

Attempting to remove elemental migration results in losing crystallites that aided in switching, reinitializing the material

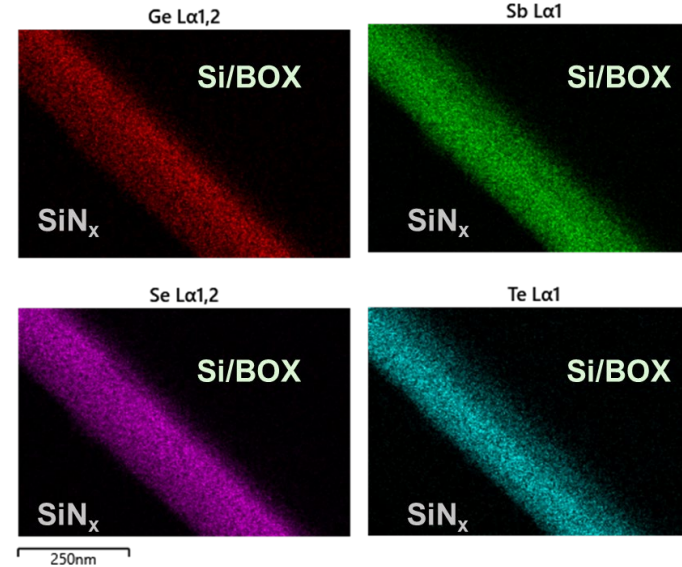
# Failure mechanisms in **optical** PCMs



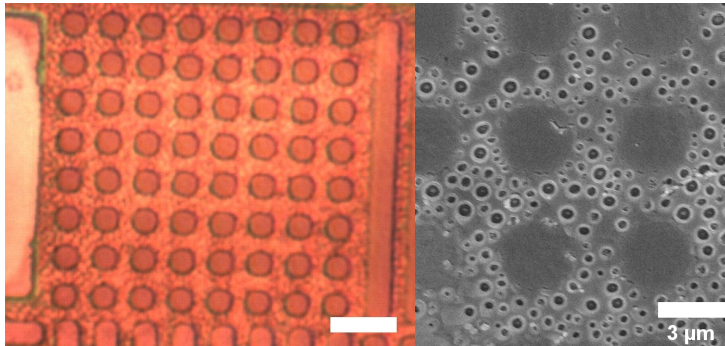
Capping layer  
delamination



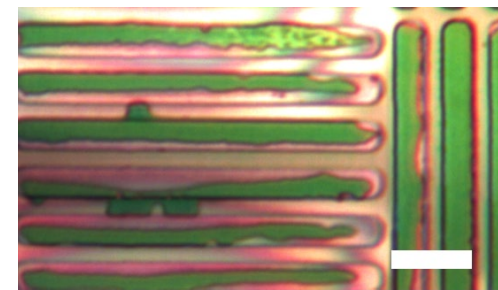
Metal contact  
electromigration



Thermo-diffusion



H-release from capping layer



Dewetting  
& fluid  
instability

# Conclusion and Outlook

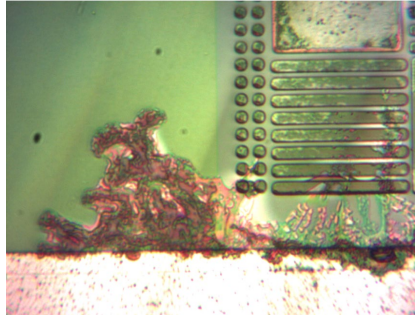
- Cycling guidelines for testing and operation
  - Continuous vs intermittent cycling
  - Heater optimization or limiting PCM operational area
  - Heat sink optimization or cool down time – limit to functionality
  - Testing of extent of amorphization and crystallization – operation in intermediate regions
- Extending life-time
  - Adhesion layers or good wettability between substrate-PCM and PCM-protective layer
  - Reducing stress in protective layers/claddings
  - PCM geometry that does not favor delamination and dewetting

# Thank you for your attention!

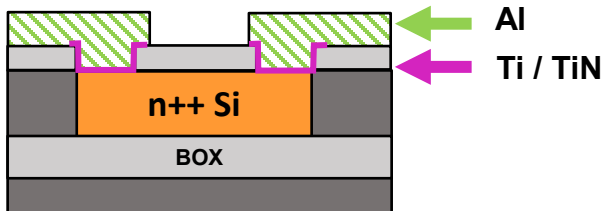
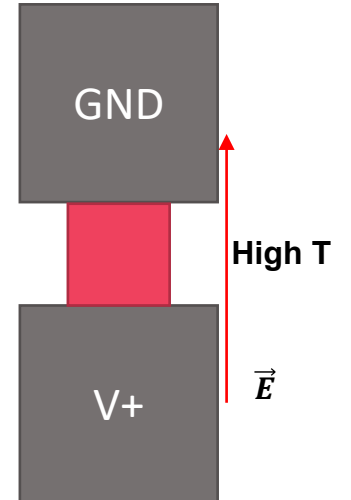
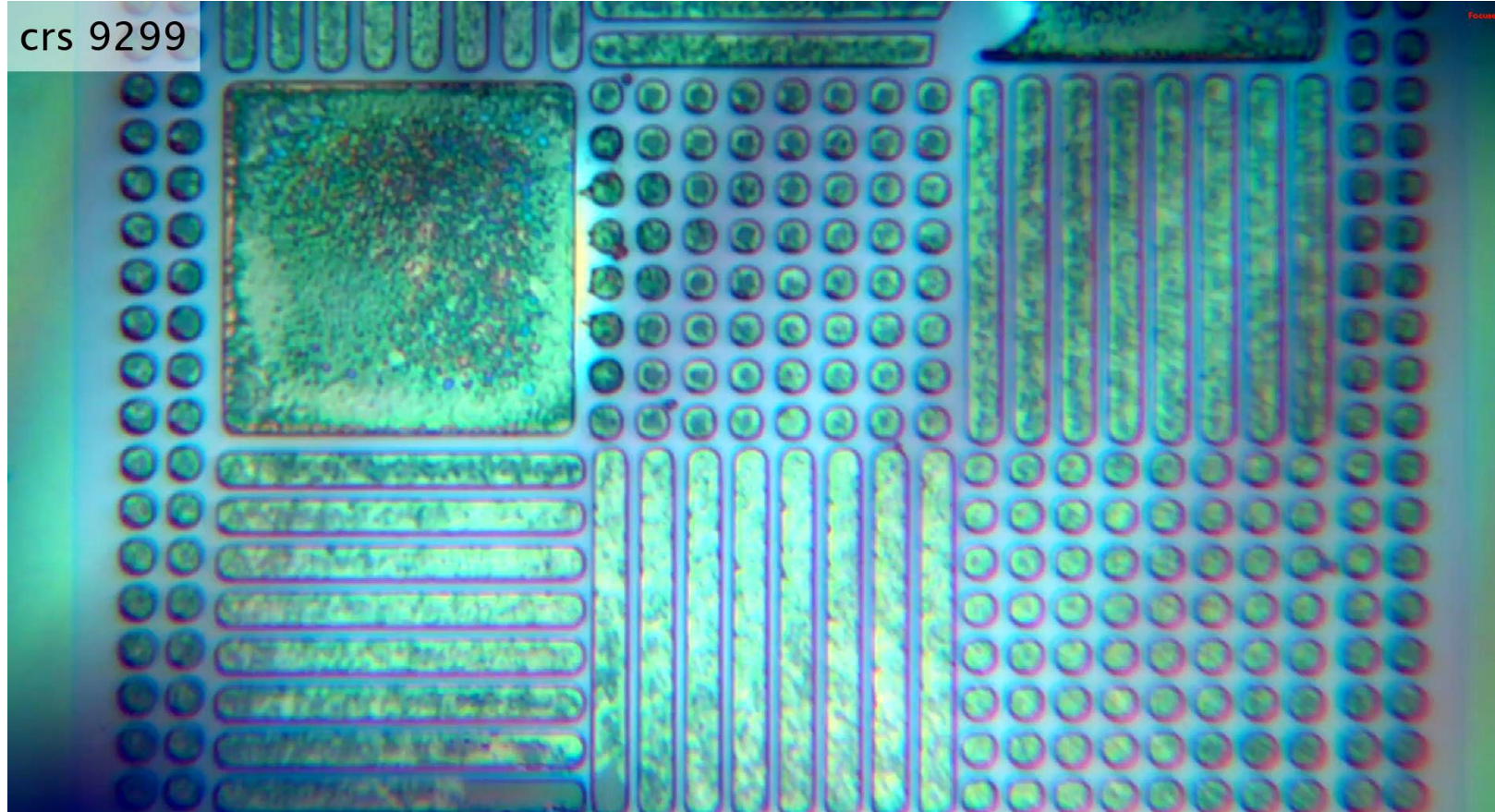


Questions?

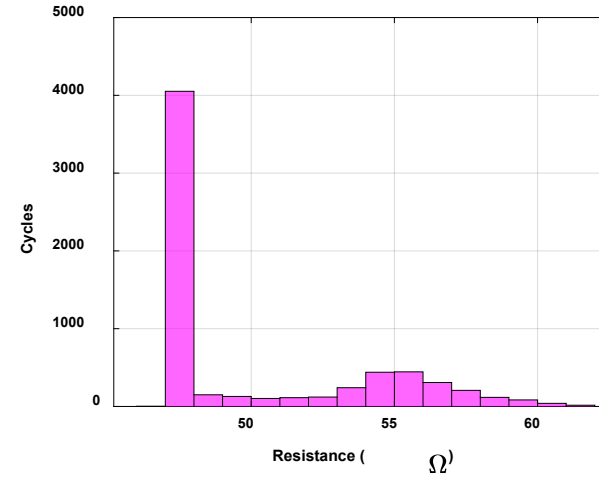
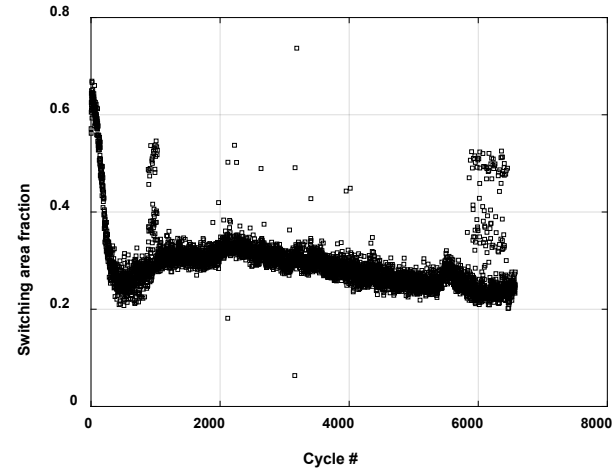
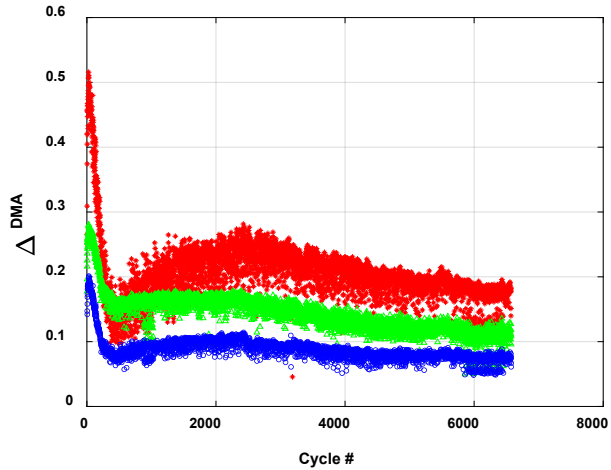
# Metal electromigration / Current crowding



Metal contact  
electromigration



# Endurance test with low/medium amorphization



## Parameters:

A 34 V 15  $\mu$ s

P 8,10,12,14 V, 0.5 s

C 18 V 0.6 s

$\bar{R} = 50 \Omega$  at 1 V

Cool down wait time avg. 55 s

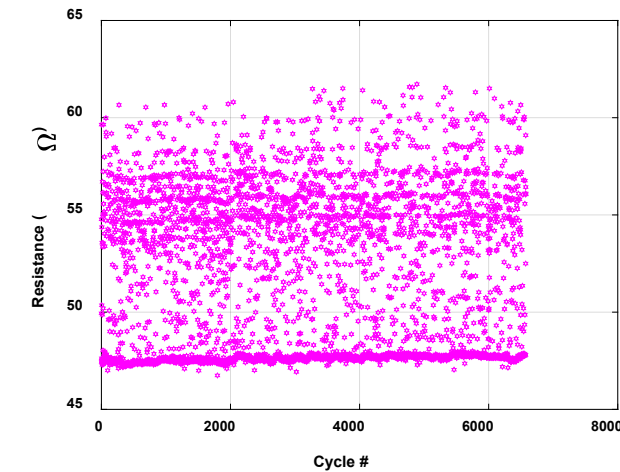
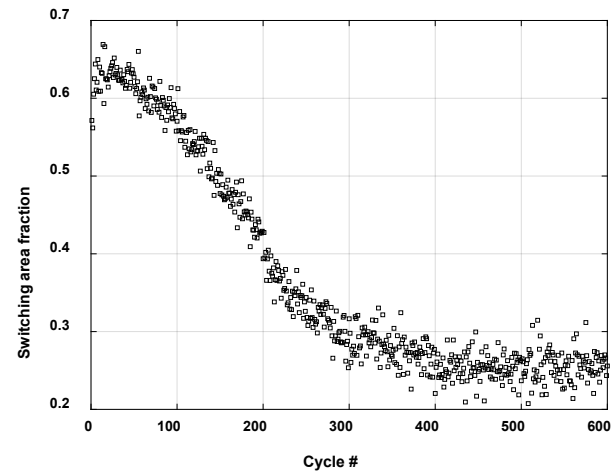
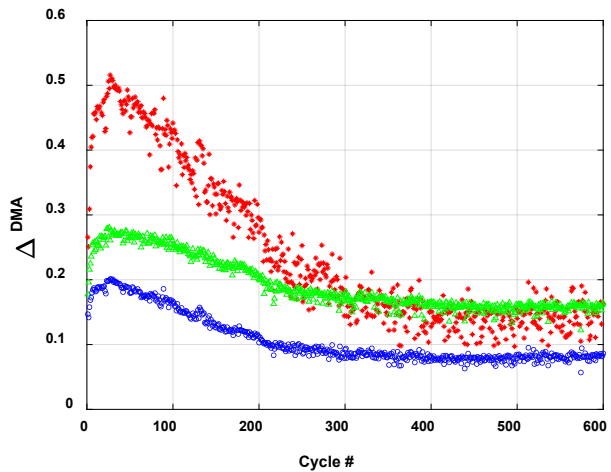
## Hypothesis:

The system will achieve a steady state contrast based on temperatures reached.

Too high temperatures – stress leads to delamination – loss of device  
Too low temperatures – low to no contrast

## Underlying mechanism:

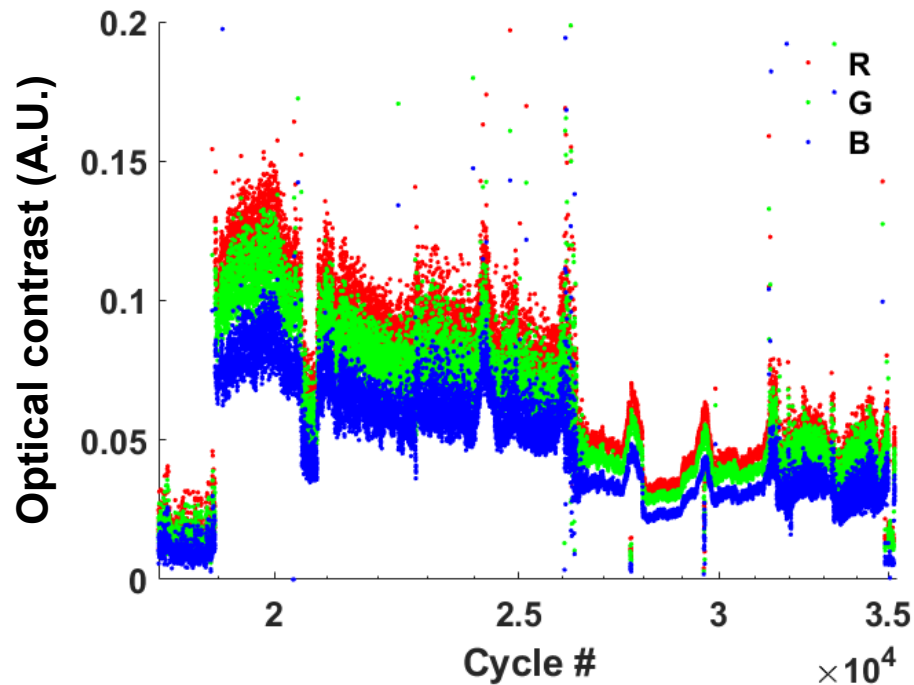
Elemental segregation



# Endurance improvement in **large-volume** optical PCM switching

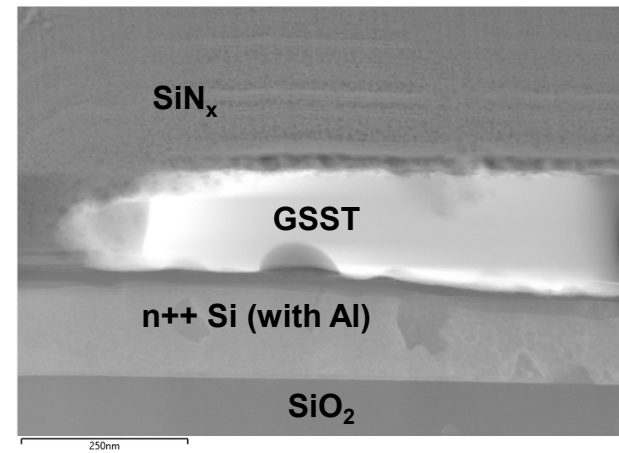
PCM switching volume:  $\sim 4,000 \mu\text{m}^3$

100 million times larger than  
that in PCMemories!

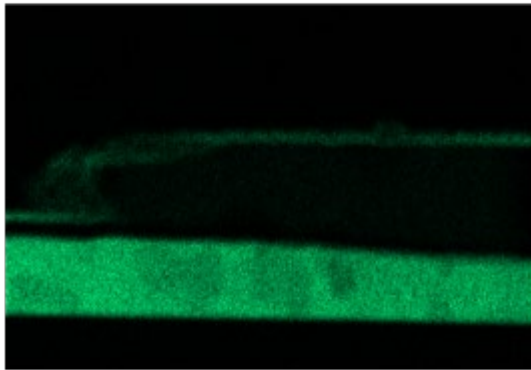


**> 35,000  
switching cycles  
demonstrated**

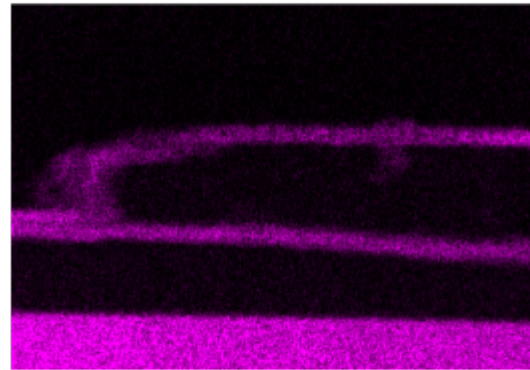
# Metal electromigration Damaged heater



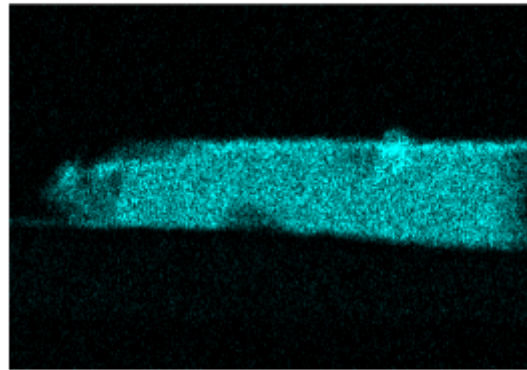
Al Kα1



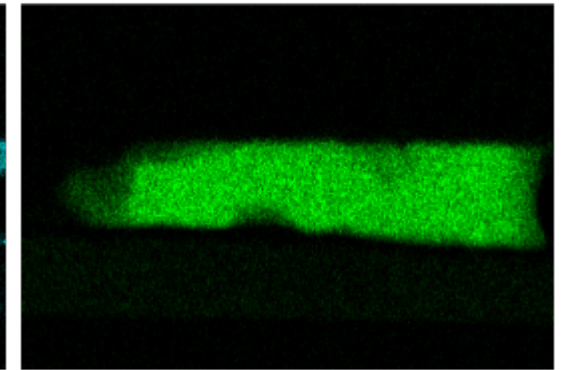
O Kα1



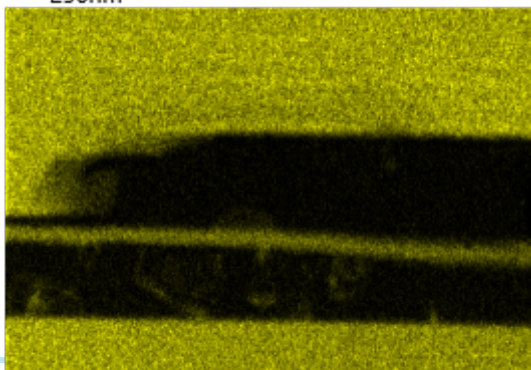
Ge Lα1,2



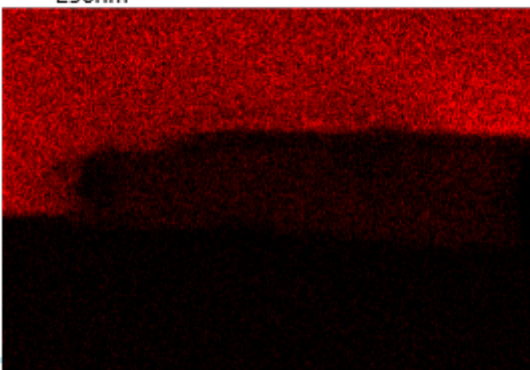
Se Lα1,2



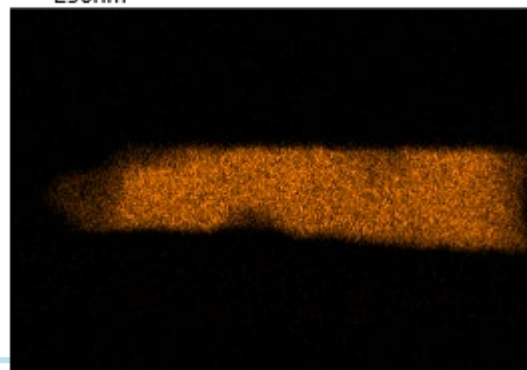
Si Kα1



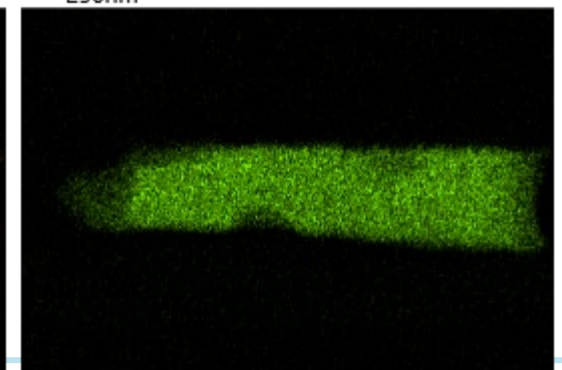
N Kα1,2



Sb Lα1



Te Lα1



# Delamination and preferential adhesion

